

SEMICONDUCTOR TECHNICAL DATA

KTN2369/A EPITAXIAL PLANAR NPN TRANSISTOR

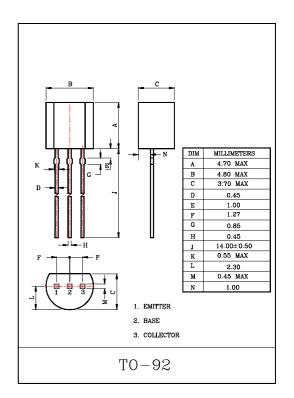
HIGH SPEED SWITCHING APPLICATION.

FEATURES

- · High Frequency Characteristics
 - : f_T =500MHz (Min.) (V_{CE} =10V, f=100MHz, I_C =10mA).
- · Excellent Switching Characteristics.
- · KTN2369/2369A Electrically Similar to 2N2369/2369A.

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Collector-Base Voltage	V_{CBO}	40	V	
Collector-Emitter Voltage	V _{CEO}	15	V	
Emitter-Base Voltage	$V_{\rm EBO}$	4.5	V	
Collector Current	I_{C}	500	mA	
Collector Power Dissipation (Ta=25℃)	Pc	625	mW	
Junction Temperature	$T_{\rm j}$	150	$^{\circ}$	
Storage Temperature Range	T_{stg}	-55~150	$^{\circ}$ C	



KTN2369/A

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTE	CRISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current		I _{CBO}	V_{CB} =20V, I_{E} =0	-	-	0.4	μΑ	
			V_{CB} =20V, I_{E} =0, Ta =125°C	-	-	30		
Collector-Base Breakdown Voltage		V _{(BR)CBO}	$I_{C}=10\mu A,\ I_{E}=0$	40	-	-		
Collector-Emitter * Breakdown Voltage		V _{(BR)CEO}	$I_E=10\text{mA},\ I_B=0$	15	-	-	V	
Emitter-Base Breakdown Voltage		V _{(BR)EBO}	$I_{E}=10\mu A,\ I_{C}=0$	4.5	-	-		
DC Current * Gain	KTN2369	- h _{FE}	I_{C} =10mA, V_{CE} =1.0V	40	_	120		
	KTN2369A			-	-	120		
	KTN2369		I _C =10mA, V _{CE} =1.0V, Ta=−55°C	20	-	-		
	KTN2369A		I _C =10mA, V _{CE} =0.35V, Ta=−55°C	20	-	-		
	KTN2369		I _C =100mA, V _{CE} =2.0V	20	-	-		
	KTN2369A		I _C =100mA, V _{CE} =1.0V	20	-	-		
Collector-Emitter * Saturation Voltage		V _{CE(sat)}	I _C =10mA, I _B =1.0mA	-	-	0.25	V	
Base-Emitter * Saturation Voltage		$V_{BE(\text{sat})}$	I _C =10mA, I _B =1.0mA	0.70	-	0.85	V	
Transition Frequency		f_{T}	I _C =10mA, V _{CE} =10V, f=100MHz	500	-	-	MHz	
Collector Output Capacitance		Соь	V_{CB} =5.0V, I_{E} =0, f=1.0MHz	-	-	4.0	рF	
Storage Time	KTN2369A	$T_{\rm stg}$	I _C =100mA, I _{B1} =-I _{B2} =10mA, V _{CC} =10V	-	-	13		
Turn-on Time		t _{on}	V _{CC} =3.0V, I _C =10mA, I _{B1} =3.0mA, I _{B2} =-1.5mA	П	-	12	nS	
Turn-off Time	KTN2369A	t_{off}	I_{C} =10mA, I_{B1} =3.0mA I_{B2} =-1.5mA, V_{CC} =3.0V	-	-	15	15	

Note : *Pulse Test : Pulse Width ≤300µS, Duty Cycle≤2.0%